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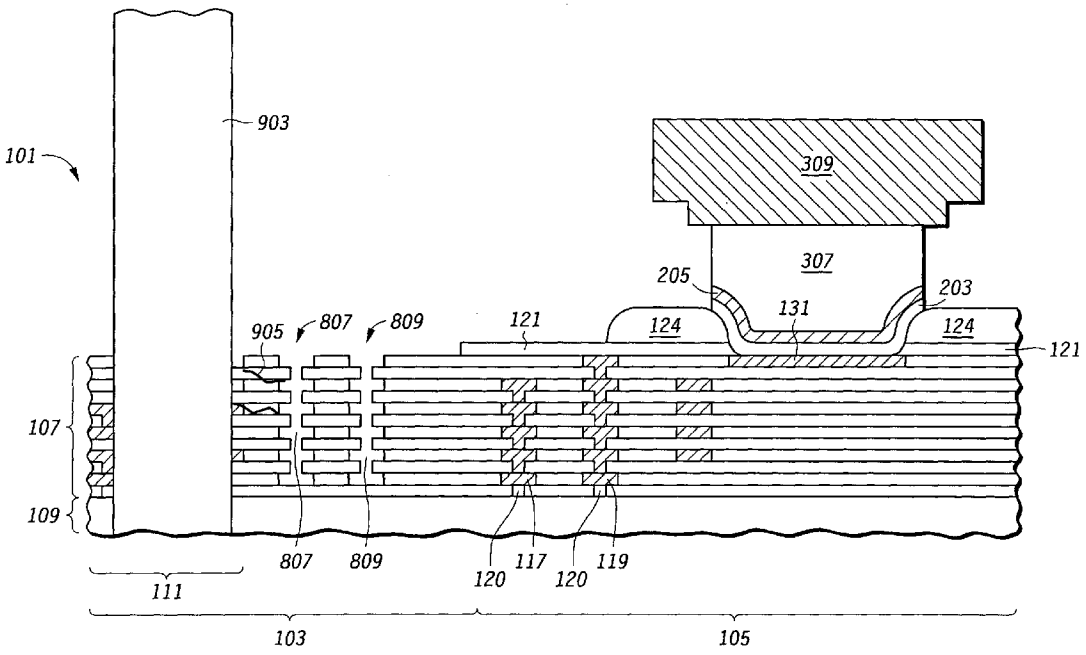
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(54) Title: METAL REDUCTION IN WAFER SCRIBE AREA



(57) Abstract: A process for removing metal from a scribe area 103 of a semiconductor wafer 101. The metal removed may include exposed metal in a saw path 111 of the scribe area and the metal in a crack stop trench of the scribe area. In one example, copper is removed from the scribe area by wet etching the wafer. In one example, the wet etching process is performed after the removal of an exposed barrier adhesion layer 203 on the wafer surface. Removal of the metal in the saw path 111 may reduce the amount of metal buildup on a saw blade 903 during singulation of the die areas 1007 of a wafer.

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